

## P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

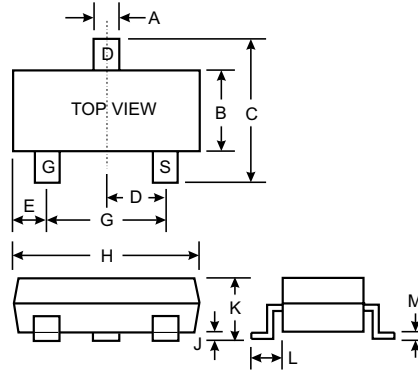
NEW PRODUCT

### Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed

### Mechanical Data

- Case: SOT-323, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Code: K84
- Weight: 0.006 grams (approx.)



SOT-323		
Dim	Min	Max
A	0.30	0.40
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.20	1.40
H	1.80	2.20
J	0.0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		

### Maximum Ratings @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	BSS84W	Units
Drain-Source Voltage	V <sub>DSS</sub>	-50	V
Drain-Gate Voltage (Note 3)	V <sub>DGR</sub>	-50	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current (Note 1)	I <sub>D</sub>	-130	mA
Total Power Dissipation (Note 1)	P <sub>d</sub>	200	mW
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 2)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-50	-75	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-15	μA	V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 25°C
		—	—	-60	μA	V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
		—	—	-100	nA	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 25°C
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±10	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 2)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.8	-1.6	-2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -1mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	6	10	Ω	V <sub>GS</sub> = -5V, I <sub>D</sub> = 0.100A
Forward Transconductance	g <sub>FS</sub>	.05	—	—	S	V <sub>DS</sub> = -25V, I <sub>D</sub> = 0.1A
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	—	45	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	—	12	pF	
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	—	10	—	ns	V <sub>DD</sub> = -30V, I <sub>D</sub> = -0.27A, R <sub>GEN</sub> = 50Ω, V <sub>GS</sub> = -10V
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	18	—	ns	

Note: 1. Valid provided that terminals are kept at specified ambient temperature.  
2. Pulse width ≤ 300μs, duty cycle ≤ 2%.